

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



28 JAN 2005



(43) International Publication Date
5 February 2004 (05.02.2004)

PCT

(10) International Publication Number
WO 2004/012218 A1

(51) International Patent Classification⁷: **H01J 1/30**, 9/02

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(21) International Application Number:
PCT/KR2003/001526

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(22) International Filing Date: 30 July 2003 (30.07.2003)

(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10-2002-0044921 30 July 2002 (30.07.2002) KR
10-2002-0058158
25 September 2002 (25.09.2002) KR

(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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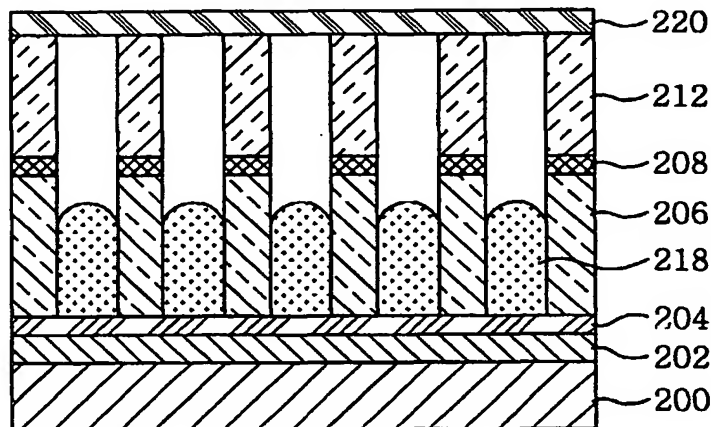
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Published:

- with international search report
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: ELECTRIC FIELD EMISSION DEVICE HAVING A TRIODE STRUCTURE FABRICATED BY USING AN ANODIC OXIDATION PROCESS AND METHOD FOR FABRICATING SAME



(57) **Abstract:** An electric field emission device having a triode structure is fabricated by using an anodic oxidation process. The device includes a supporting substrate, a bottom electrode layer to be used as a cathode electrode of the device, a gate insulating layer having a plurality of first sub-micro holes, a gate electrode layer having a plurality of second sub-micro holes connecting to the first sub-micro holes, an anode insulating layer having a plurality of third sub-micro holes connecting to the second sub-micro holes, a top electrode layer for hermetically sealing the device, the top electrode layer being used as an anode of the device and a plurality of emitters formed in the first sub-micro holes. The emitters are formed so as to come into as close contact as possible to the electrodes of the device, which results in decreasing a driving voltage

for the device.

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